

substance: OsSi₂

property: physical properties

energy gaps

$E_{g,th}$	> 0.26 eV		from $\log \rho \propto E_g/2kT$; $T = 400...700$ K, sintered sample	82H
	1.8 eV		from $\log \rho \propto E_g/2kT$; $T = 1000...1370$ K, p-type sintered sample containing 1.5 at% Al and 0.2 at% Fe; dc four-probe method with Mo contacts	83M
E_g	2 eV	RT	on sintered sample as above optical reflectivity similar to that of FeSi ₂ ; thermoelectric power (+ 100 $\mu V K^{-1}$ at 300 K, + 400 $\mu V K^{-1}$ at 900 K) decreasing above 1000 K	

References:

- 82H Hulliger, F.: unpublished.
83M Mason, K., Müller-Vogt, O.: J. Cryst. Growth 63 (1983) 34.